Department of Electronic Control Engineering



Development of Ferroelectric Crystal Materials Measurement of Ferroelectric Properties for Relaxor _{Kazuhiko FUJITA}

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Keywords

Relaxor ferroelectrics, Piezoelectrics, permittivity

Research Outline

Crystal Growth of Relaxor typed Ferroelectrics

The ferroelectric materials are widely used as a key material of the electronic devices like a piezoelectric device, an ultrasonic transducer, or a FeRAM (ferroelectric random access memory), etc.. Relaxor typed ferroelectric crystals like (1-x)Pb(Zn1/3Nb2/3)O3-xPbTiO3 (abbr. (1-x)PZN-xPT) are grown with PbO flux by the flux method in electric furnace. The photograph below shows 0.95PZN-0.05PT single crystals grown in this method.





0.95PZN-0.05PT single crystals



Capacitor sample



Magnetron Sputter

Measurement of the Ferroelectric properties and Piezoelectric properties for the ferroelectric materials

(1-x)PZN-*x*PT crystals are polished using lapping paper, shaped to the thin plate. After that, the electrodes are sputtered on the both sides of (1-x)PZN*x*PT plate. The (1-x)PZN-*x*PT sample are formed into the capacitor. Using an impedance analyzer (HP4194A) and thermostatic furnace, the temperature dependence of the permittivity of the (1-x)PZN-*x*PT material is measured. The temperature dependence of the permittivity for 0.93PZN-0.07PT crystal in cooling process is shown in the following figure.





Temperature dependence of permittivity for 0.93 PZN-0.07PT

Impedance Analyzer